MJE13009

NPN SILICON TRANSISTOR

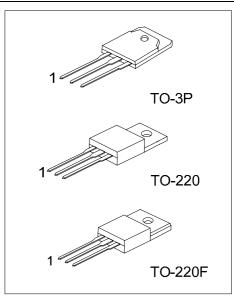
SWITCHMODE SERIES NPN SILICON POWER **TRANSISTORS**

DESCRIPTION

The MJE13009 is designed for high-voltage, high-speed power switching inductive circuits where fall time is critical. They are particularly suited for 115 and 220 V switch mode applications such as Switching Regulators, Inverters, Motor Controls, Solenoid/Relay drivers and Deflection circuits.

FEATURES

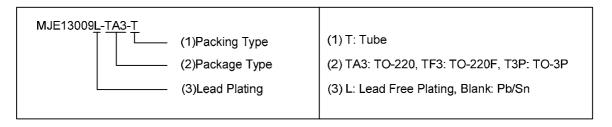
- * V_{CEO} 400 V and 300 V
- * Reverse Bias SOA with Inductive Loads @ T_C = 100
- * Inductive Switching Matrix 3 ~ 12 Amp, 25 and 100 tc @ 8 A, 100 is 120 ns (Typ).
- * 700 V Blocking Capability
- * SOA and Switching Applications Information.



*Pb-free plating product number:MJE13009L

ORDERING INFORMATION

Order Number		Dookogo	Pin Assignment			Dooking	
Normal	Lead Free Plating	Package	1	2	3	Packing	
MJE13009-TA3-T	MJE13009L-TA3-T	TO-220	В	С	E	Tube	
MJE13009-TF3-T	MJE13009L-TF3-T	TO-220F	В	C	Е	Tube	
MJE13009-T3P-T	MJE13009L-T3P-T	TO-3P	В	C	Е	Tube	



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■ ABSOLUTE MAXIMUM RATINGS (Ta = 25

PARAMETER	SYMBOL	RATINGS	UNIT	
Collector-Emitter Voltage	V_{CEO}	400	V	
Collector-Emitter Voltage (V _{BE} =-1.5V)	$V_{\sf CEV}$	700	V	
Emitter Base Voltage	V_{EBO}	9	V	
Callagter Current	Continuous	Ic	12	^
Collector Current	Peak*	I _{CM}	24	A
Dago Current	Continuous	lΒ	6	
Base Current	Peak*	I _{BM}	12	A
Englisher Command	Continuous	Ι _Ε	18	
Emitter Current	Peak*	I _{EM}	36	Α
Total Power Dissipation @ Ta = 25	Б	2	W	
Derate above 25	P _D	16	mW/	
Total Power Dissipation @ T_C = 25 Derate above 25			100	W
		P _D	800	mW/
Junction Temperature		ΤJ	+150	
Storage Temperature	T _{STG}	-40 ~ +150		

Note: 1. Pulse Test: Pulse Width = 5ms, Duty Cycle ≤ 10%

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Thermal Resistance Junction to Ambient	θ_{JA}	54	/W
Thermal Resistance Junction to Case	θЈС	4	/W

■ ELECTRICAL CHARACTERISTICS (T_C= 25 , unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT		
*OFF CHARACTERISTICS								
Collector- Emitter Sustaining Voltage	V_{CEO}	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$	400			V		
Collector Cutoff Current		$V_{BE(OFF)} = 1.5Vdc$			1	mA		
V _{CBO} =Rated Value	I _{CEV}	$V_{BE(OFF)} = 1.5Vdc, T_C = 100$			5	ША		
Emitter Cutoff Current	I _{EBO}	$V_{EB} = 9Vdc, I_C = 0$			1	mA		
*ON CHARACTERISTICS								
DC Current Gain	h _{FE1}	$I_C = 5A, V_{CE} = 5V$			40			
DC Current Gain	h _{FE 2}	$I_C = 8A, V_{CE} = 5V$			30			
		$I_{C} = 5A, I_{B} = 1A$			1	V		
Current-Emitter Saturation Voltage	V _{CE(SAT)}	$I_C = 8A, I_B = 1.6A$			1.5	V		
Current-Emilier Saturation Voltage	V CE(SAT)	$I_{\rm C} = 12A, I_{\rm B} = 3A$			3	V		
		$I_C = 8A$, $I_B = 1.6A$, $T_C = 100$			2	V		
	$V_{BE(SAT)}$	$I_{C} = 5A, I_{B} = 1A$			1.2	V		
Base-Emitter Saturation Voltage		$I_C = 8A, I_B = 1.6A$			1.6	V		
_		$I_C = 8A$, $I_B = 1.6A$, $T_C = 100$			1.5	V		
DYNAMIC CHARACTERISTICS				•				
Transition frequency	f⊤	I _C = 500mA, V _{CE} = 10V, f = 1MHz	4			MHz		
Output Capacitance	C_ob	$V_{CB} = 10V$, $I_E = 0$, $f = 0.1MHz$		180		pF		
SWITCHING CHARACTERISTICS (Re	esistive Load	, Table 1)						
Delay Time	t _{DLY}	\/ - 105\/do - 00		0.06	0.1	μs		
Rise Time	t _R	V _{CC} = 125Vdc, I _C = 8A		0.45	1	μs		
Storage Time	ts	l _{Β1} = l _{Β2} = 1.6A, t _P = 25μs Duty Cycle ≤1%		1.3	3	μs		
Fall Time	Time t _F Buty Gycle 3176			0.2	0.7	μs		
Inductive Load, Clamped (Table 1, F	igure 13)							
Voltage Storage Time	ts	I _C =8A, V _{clamp} =300V, I _{B1} =1.6A		0.92	2.3	μs		
Crossover Time	tc	$V_{BE(OFF)} = 5V$, $T_C = 100$		0.12	0.7	μs		

^{*}Pulse Test: Pulse Wieth = 300µs, Duty Cycle = 2%

^{2.} Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ TABLE 1. TEST CONDITIONS FOR DYNAMIC PERFORMANCE

	REVERSE BIAS SAFE OPERATING AREA AND INDUCTIVE SWITCHING	RESISTIVE SWITCHING		
TEST CIRCUITS	DUTY CYCLE 10% $_{1N4933}$ $_{33}$ $_{33}$ $_{33}$ $_{33}$ $_{33}$ $_{33}$ $_{33}$ $_{33}$ $_{33}$ $_{33}$ $_{33}$ $_{33}$ $_{33}$ $_{33}$ $_{34}$ $_{33}$ $_{34}$ $_{33}$ $_{34}$ $_{34}$ $_{33}$ $_{34}$ $_$	+125V R _C TUT SCOPE -4.0V		
CIRCUIT VALUES	Coil Data: Ferroxcube Core #6656 GAP for 200 μ H/20 A V_{CC} = 20 V Full Bobbin (~16 Turns) #16 L_{coil} = 200 μ H V_{clamp} = 300 Vdc	V_{CC} = 125 V R_{C} = 15 Ω D1 = 1N5820 or Equiv. R_{B} = Ω		
TEST WAVEFORMS	OUTPUT WAVEFORMS $t_{F} \text{ CLAMPED}$ $t_{F} \text{ UNCLAMPED 9 } t_{2} \qquad t_{1} \text{ ADJUSTED TO}$ $OBTAIN IC$ $t_{1} \frac{L_{coil} (I_{CM})}{V_{CC}} \qquad Test \text{ Equipment}$ $Scope-Tektronics$ $475 \text{ or Equivalent}$ $TIME $	$t_{\rm R},t_{\rm F}$ < 10 ns Duty Cycle = 1.0% R _B and R _C adjusted for desired l _B and l _C		

■ TABLE 2. APPLICATIONS EXAMPLES OF SWITCHING CIRCUITS

CIRCUIT	LOAD LINE DIAGRAMS	TIME DIAGRAMS
SERIES SWITCHING REGULATOR Vcc Vout	TURN-ON (FORWARD BIAS) SOA $to_{N} \leqslant 10 \text{ ms}$ DUTY CYCLE $\leqslant 10\%$ $P_{D} = 4000 \text{ W (2)}$ TURN-OFF (REVERSE BIAS) SOA $1.5 \text{ V} \leqslant \text{V}_{\text{BE(off)}} \leqslant 9.0 \text{ V}$ DUTY CYCLE $\leqslant 10\%$ COLLECTOR VOLTAGE	TIME t VCE VCC TIME t
RINGING CHOKE INVERTER Vcc Vout	TURN-ON (FORWARD BIAS) SOA $ \begin{array}{cccccccccccccccccccccccccccccccccc$	V _{CE} LEAKAGE SPIKE V _{CC} N(V _O) V _{CC} toff toff toff toff toff toff toff tof
PUSH-PULL INVERTER/CONVERTER Vout	TURN-ON (FORWARD BIAS) SOA $t_{ON} \leqslant 10 \text{ ms}$ DUTY CYCLE $\leqslant 10\%$ $T_C = 100^{\circ}\text{C}$ $P_D = 4000 \text{ W (2)}$ $350V$ $12A$ $TURN-OFF \text{ (REVERSE BIAS) SOA}$ $1.5 \text{ V } \leqslant V_{BE(off)} \leqslant 9.0 \text{ V}$ DUTY CYCLE $\leqslant 10\%$ V_{CC} $400V \text{ (1)}$ $TOOV \text{ (1)}$ $COLLECTOR \text{ VOLTAGE}$	V _{CE} V _{CC} V _{CC} toN toFF t t
SOLENOID DRIVER Vcc SOLENOID	TURN-ON (FORWARD BIAS) SOA t_{ON} 10 ms DUTY CYCLE 10% $T_{C} = 100^{\circ}\text{C}$ $T_{C} = 4000 \text{ W } \text{(2)}$ TURN-OFF (REVERSE BIAS) SOA 1.5 V $t_{BE(off)}$ 9.0 V DUTY CYCLE 10% TURN-ON 2 t_{ON} TURN-OFF TURN-ON 7 700V (1) COLLECTOR VOLTAGE	V _{CE} V _{CC} t _{ON} t _{OFF} t

■ TABLE 3. TYPICAL INDUCTIVE SWITCHING PERFORMANCE

I _C (A)	T _C ()	t _{sv} (ns)	t _{rv} (ns)	t _{fi} (ns)	t _{ti} (ns)	t _c (ns)
3	25	770	100	150	200	240
3	100	1000	230	160	200	320
_	25	630	72	26	10	100
5	100	820	100	55	30	180
	25	720	55	27	2	77
8	100	920	70	50	8	120
10	25	640	20	17	2	41
12	100	800	32	24	4	54

SWITCHING TIME NOTES

In resistive switching circuits, rise, fall, and storage times have been defined and apply to both current and voltage

waveforms since they are in phase. However, for inductive loads which are common to SWITCHMODE power supplies and hammer drivers, current and voltage waveforms are not in phase. Therefore, separate measurements must be made on each waveform to determine the total switching time. For this reason, the following new terms have been defined.

 t_{sv} = Voltage Storage Time, 90% I_{B1} to 10% V_{CEM}

t_{rv} = Voltage Rise Time, 10–90% V_{CEM}

t_{fi} = Current Fall Time, 90–10% I_{CM}

t_{ti} = Current Tail, 10–2% I_{CM}

 t_c = Crossover Time, 10% V_{CEM} to 10% I_{CM}

An enlarged portion of the turn-off waveforms is shown in Figure 13 to aid in the visual identity of these terms.

For the designer, there is minimal switching loss during storage time and the predominant switching power losses occur during the crossover interval and can be obtained using the standard equation from AN–222:

 $P_{SWT} = 1/2 V_{CC}I_{C}(t_{c}) f$

Typical inductive switching waveforms are shown in Figure 14. In general, $t_{rv} + t_{fi}$ t_c . However, at lower test currents this relationship may not be valid.

As is common with most switching transistors, resistive switching is specified at 25 $\,$ and has become a benchmark for designers. However, for designers of high frequency converter circuits, the user oriented specifications which make this a "SWITCHMODE" transistor are the inductive switching speeds (t_c and t_{sv}) which are guaranteed at 100 $\,$.

■ TYPICAL CHARATERISTICS

Figure 1. Forward Bias Safe Operating Area

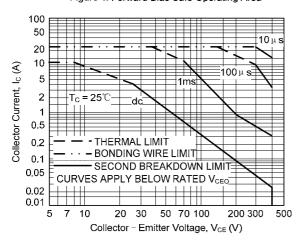


Figure 3. Forward Bias Power Derating

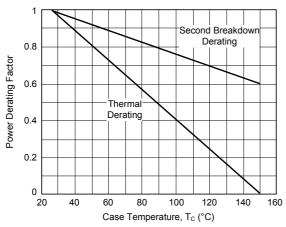
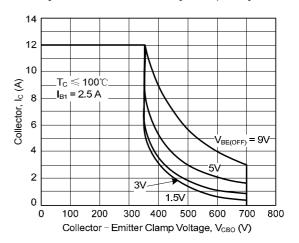


Figure 2. Reverse Bias Switching Safe Operating Area

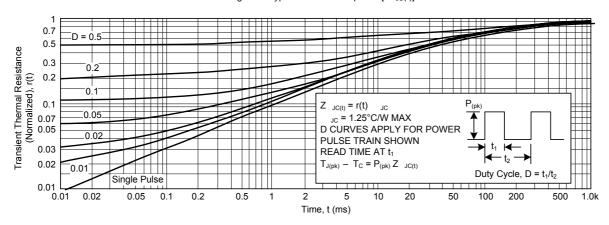


There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $l_{\text{c}}-V_{\text{CE}}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on $T_{\text{C}}=25$; $T_{\text{J(pk)}}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when $T_{\text{C}}=25$ Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on Figure 1 may be found at any case temperature by using the appropriate curve on Figure 3.

 $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown. Use of reverse biased safe operating area data (Figure 2) is discussed in the applications information section.

Figure 4. Typical Thermal Response [Z JC(t)]



■ TYPICAL CHARACTERISTICS (Cont.)

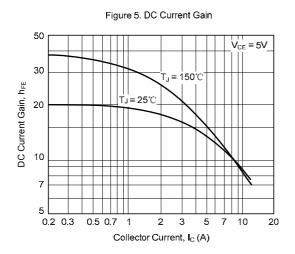
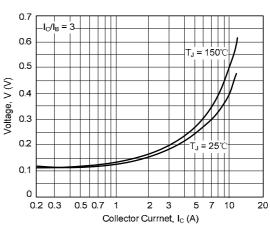
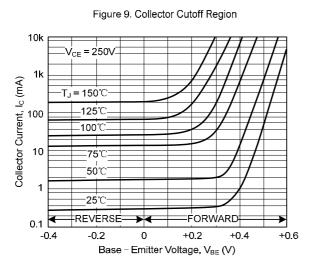


Figure 6. Collector Saturation Region

2
1.6
1.6
1.2
1.0
0.8
0.0050.07 0.1
0.2 0.3 0.5 0.7 1 2 3 5

Base Current, I_B (A)





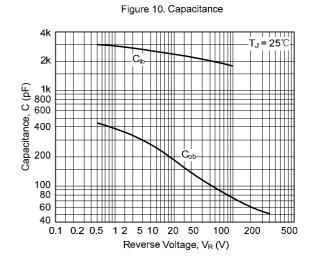
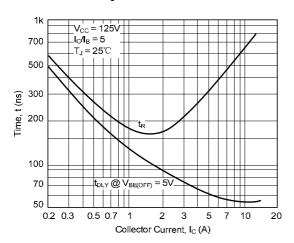


Figure 8. Collector - Emitter Saturation Voltage

RESISTIVE SWITCHING PERFORMANCE

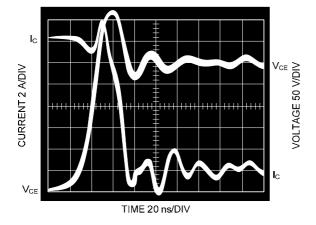
Figure 11. Turn - On Time



Collector Crrent, I_C (A)

Figure 12. Turn - Off Time

Figure 13. Typical Inductive Switching Waveforms (at 300V and 12A with I_{B1} = 2.4A and $V_{BE(off)}$ = 5V)



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